

L Number	Hits	Search Text	DB	Time stamp
1	125	(method with yaw with sensor).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 16:23
2	1023	(method with accelerometer).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 16:24
3	60	(method with accelerometer).clm. and MEMS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 16:27
4	382	(438/50).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 16:27
5	631	(438/48).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 16:27
6	428	(438/52).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 16:27
7	62	((438/50).CCLS.) and protect\$3.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 16:28
8	66	((Ge or Germanium) with (etch\$3 or attack\$3) with (KOH or (potassium adj hydroxide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 17:35
9	85	((releas\$3 with etch\$3) with (KOH or (potassium adj hydroxide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 17:35
10	62	((silicon-germanium) with protect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 17:38
-	44	((Ge or Germanium) same (protect\$3 adj (coating or layer or material or film))) and ((polysilicon or nucleat\$3) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 17:21
-	62	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and ((pattern\$3 or etch\$3 or remov\$3 or form\$3) with (backside or back-side)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/08 19:22
-	102	(sensor\$1 or transducer\$1).clm. and ((pattern\$3 or etch\$3 or remov\$3 or form\$3) with (backside or back-side)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/08 19:21
-	36	(Ge or Germanium) with (nucleat\$3 adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 11:35

-	389	MEMS and etch\$3 and (sacrificial).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/12 09:10
-	112	((216/2).CCLS.) and (protect\$3).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/08 19:23
-	142	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (etch\$3 and (protective adj layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 11:54
-	2	("6368885").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 11:35
-	6	("5527744" "5903380" "6080675" "6140689" "6204087" "6225145").PN.	USPAT	2004/10/12 11:35
-	0	6368885.URPN.	USPAT	2004/10/12 11:36
-	25	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (etch\$3 and (aluminum adj layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 11:42
-	219	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (etch\$3 and ((protect\$3 or etch-resist\$3 or etch-stop) adj layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 11:44
-	16	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (etch\$3 and (back-side or backside or (back adj side)) and ((protect\$3 or etch-resist\$3 or etch-stop) adj layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 11:47
-	12	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (etch\$3 and (back-side or backside or (back adj side)) and ((aluminum or polysilicon) adj layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 11:48
-	43	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (etch\$3 and (release adj (mask or layer))).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 11:57
-	21	(release adj mask).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 11:58
-	108	(protect\$3 or preveent\$3) and (etch\$3 and mask\$3 and backside).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 12:00
-	91	(MEMS microstructure\$1) and ((pattern\$3 or etch\$3 or remov\$3 or form\$3) with (backside or back-side)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/12 14:38